MGFC42V5258

Unit: millimeters

24+/-0.3

5.2 - 5.8GHz BAND 16W INTERNALLY MATCHED GaAs FET

OUTLINE DRAWING

DESCRIPTION

The MGFC42V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 - 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation
Internally matched to 50(ohm) system
High output power
P1dB = 16W (TYP.) @ f=5.2 - 5.8 GHz
High power gain
GLP = 10.5 dB (TYP.) @ f=5.2 - 5.8GHz
High power added efficiency
P.A.E. = 31 % (TYP.) @ f=5.2 - 5.8GHz

APPLICATION

5.2 - 5.8 GHz band power amplifier

QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V) ID = 4.5 (A) RG=25 (ohm)

ABSOLUTE MAXIMUM RATINGS

(Ta=25deg.C)

GF-18

Symbol	Parameter	Ratings	Unit			
VGDO	Gate to drain voltage	-15	V			
VGSO	Gate to source voltage	-15	V			
ID	Drain current	15	Α			
IGR	Reverse gate current	-40	mA			
IGF	Forward gate current	84	mA			
PT	Total power dissipation *1	78.9	W			
Tch	Channel temperature	175	deg.C			
Tstg	Storage temperature	-65 / +175	deg.C			
*4. T. 05 b. 0						

^{*1 :} Tc=25deg.C

R1.25 (1) 0.6+/-0.15 (2) 8/91 (2): SOURCE (FLANGE)

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(3): DRAIN

ELECTRICAL CHARACTERISTICS (Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits		Unit	
-			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS = 3V , VGS = 0V	-	9	12	Α
gm	Transconductance	VDS = 3V , ID = 4.4A	-	4	-	S
VGS(off)	Gate to source cut-off voltage	VDS = 3V , ID = 80mA	-2	-3	-4	V
P1dB	Output power at 1dB gain compression		41.5	42.5	-	dBm
GLP	Linear power gain	VDS=10V, ID(RF off)=4.5A, f=5.2 - 5.8GHz	8	10.5	-	dB
ID	Drain current		-	4.5	-	Α
P.A.E.	Power added efficiency		-	31	-	%
Rth(ch-c)	Thermal resistance *1	delta Vf method	-	-	1.9	deg.C/W

^{*1 :} Channel-case



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